Serial No. 10/615,818 Docket No. NEC 198130 DIV Amendment B

## **AMENDMENTS TO THE SPECIFICATION:**

Please amend the paragraph beginning at page 1, line 3, as follows:

Cross Reference to Related Application

This Application is a divisional of U.S. Application Serial No. 09/613,476, filed July 11, 2000, now U.S. Patent No. 6,636,281, issued October 21, 2003.

Please amend the paragraph bridging pages 25 and 26, beginning at page 25, line 16, as follows:

The wide slit 10 may be considered as is similar to a combination of the main slit 7 and the sub slit 8 of the first embodiment shown in FIG. 4. That is, in the third embodiment, the wide slit 10 is formed over a region of the TCP 2, which corresponds to the region covering the main slit 7 and the sub slit 8 and the region between the slits 7 and 8 of the first embodiment, with an insulating film 23 thinner than the insulating film 23 of the first embodiment such that the portion of the wide slit 10 is easily bent as a whole. Therefore, a region 102 of the wide slit 10 in the vicinity of the liquid crystal panel 1 corresponds in function to the sub slit 8 in the first embodiment and only a region 100 of the wide slit 10 in the bent portion of the TCP 2 corresponds in function to the main slit 7.

Please insert the following new paragraph beginning at page 26, line 3, as follows:

--Also, as in FIGs. 5A-5C, the distance d1 between the center of the main slit portion 100 and the center of the sub slit portion 102 may be any, provided that it is larger than a depth d2 of the hook portion 6 (as shown in FIGs. 12A-12C), that is, a vertical distance for which the circuit substrate is to be pulled up.--

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